# **Monolithic Amplifier Die**

MAR-8A-D+

50 $\Omega$  DC to 1 GHz

# **The Big Deal**

- High gain, 31.5 dB at 0.1 GHz
- High IP3, up to +25 dBm
- Low noise figure, 3.1 dB typ up to 1 GHz



# **Product Overview**

MAR-8A-D+ is a wideband amplifier Die offering high gain and low noise figure. It has repeatable performance from lot to lot. MAR-8A-D+ uses Darlington configuration and is fabricated using InGaP HBT technology.

**Key Features** 

Feature	Advantages
High Gain, 31 dB typ. at 0.1GHz	The MAR-8A-D+ provides high gain eliminating need for multiple stages reducing cost and real estate. Minimizes the effect of noise figure follow up stages on overall noise figure.
High Dynamic Range Low Noise Figure, 3.1dB typ. up to 1 GHz High IP3, +25 dBm	Combination of low noise and high IP3 makes this MMIC amplifier die ideal for use in low noise receiver front end (RFE) as it gives the user advantages of sensitivity and two-tone IM performance at both ends of the dynamic range.
Unpackaged die	Enables the user to integrate the amplifier directly into hybrids.

# **Monolithic Amplifier Die**

# MAR-8A-D+

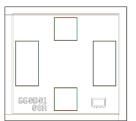
### 50 $\Omega$ DC to 1 GHz

### **Product Features**

- High gain, 31.5 dB at 0.1 GHz, reduces component count
- Internally Matched to 50 Ohms
- High power output, +12.5 dBm typ.
- Low noise
- Improved stability
- Protection against power supply transients
- Protected by US Patent 6,943,629

# **Typical Applications**

- Cellular Infrastructure
- UHF/VHF transmitters/receivers



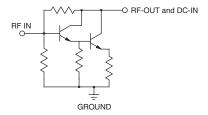
+RoHS Compliant
The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

Ordering Information: Refer to Last Page

# **General Description**

MAR-8A-D+ (RoHS compliant) is a wideband amplifier Die offering high gain and low noise figure. It has repeatable performance from lot to lot. MAR-8A-D+ uses Darlington configuration and is fabricated using InGaP HBT technology.

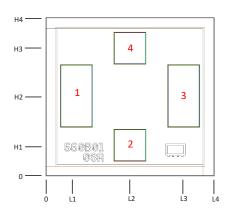
# Simplified Schematic and Pad description



Pad #	Function	Description
4	RF IN	RF input pad. This pad requires the use of an external DC blocking capacitor chosen for the frequency of operation.
2	RF-OUT and DC-IN	RF output pad and bias pad. DC voltage is present on this pad, therefore, a DC blocking capacitor is necessary for proper operation.  An RF choke is needed to feed DC bias without loss of RF signal due to the bias connection.
1,3	GROUND	Connections to ground.

Note: 1. Bond Pad material - Gold 2. Bottom of Die - Gold plated

# **Bonding Pad Position**



Dimensions	in	μm,	Typical
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L1	L2	L3	L4	H1	H2	НЗ	H4	Thickness	Bond Pad Size (RF In, RF Out and DC In)	Ground Pad Size
95	260	425	520	95	248	395	490	100	100 x 100	100 x 195



### Electrical Specifications<sup>1</sup> at 25°C and 35mA, unless noted

Parameter		Min.	Тур.	Max.	Units
Frequency Range <sup>2</sup>		DC		1	GHz
Gain	f=0.1 GHz		31.5	_	dB
	f=1 GHz		25	_	
Input Return Loss	f=DC to 1 GHz		15.5		dB
Output Return Loss	f=DC to 1 GHz		11		dB
Output Power @ 1 dB compression	f=1 GHz		+12.5		dBm
·					
Output IP3	f=1 GHz		+25		dBm
Noise Figure	f=1 GHz		3.1		dB
Recommended Device Operating Current			36		mA
Device Operating Voltage		3.2	3.7	4.2	V
Device Voltage Variation vs. Temperature at 36 mA			+1.2		mV/°C
Device Voltage Variation vs. Current at 25°C			11.3		mV/mA
Thermal Resistance, junction-to-case <sup>3</sup>			119		°C/W

<sup>1.</sup> Measured on Mini-Circuits characterization test board. Die packaged in a plastic micro-x package and soldered on test board TB-432-8A+. See characterization test circuit (Fig. 1) 2. Guaranteed specification DC-1 GHz. Low frequency cut off determined by external coupling capacitors.

# **Absolute Maximum Ratings<sup>4</sup>**

Parameter	Ratings
Operating Temperature	-40°C to 85°C
Operating Current	65mA
Power Dissipation	250mW
Input Power	13dBm

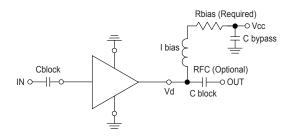
Permanent damage may occur if any of these limits are exceeded. These ratings are not intended for continuous normal operation.



<sup>3.</sup> Case is defined as ground leads.

<sup>&</sup>lt;sup>4</sup> Full temperature range.

# **Recommended Application and Characterization Test Circuit**



Test Board includes case, connectors, and components (in bold) soldered to PCB

R BIAS				
Vcc	Bias Resistor Value <sup>1</sup>			
7	88.7			
8	118			
9	143			
10	174			
11	200			
12	226			
13	255			
14	280			
15	309			

1. 1% resistor values (ohms) for optimum bias.

Fig 1. Block Diagram of Test Circuit used for characterization. (DUT, Die packaged in plastic micro-x package, soldered on Mini-Circuits Characterization test board TB-432-8A+)

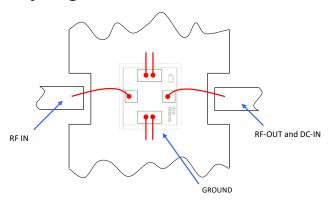
Gain, Return loss, Output power at 1dB compression (P1 dB), output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

#### Conditions:

1. Gain and Return loss: Pin= -25dBm.

Output IP3 (OIP3): Two tones, spaced 1 MHz apart, -5 dBm/tone at output.

# **Assembly Diagram**



### **Assembly and Handling Procedure**

### 1. Storage

Dice should be stored in a dry nitrogen purged desiccators or equivalent.

#### 2. ESI

MMIC HBT amplifier dice are susceptible to electrostatic and mechanical damage. Die are supplied in antistatic protected material, which should be opened in clean room conditions at an appropriately grounded anti-static worksta tion. Devices need careful handling using correctly designed collets, vacuum pickup tips or sharp antistatic tweezers to deter ESD damage to dice.

#### 3. Die Attach

The die mounting surface must be clean and flat. Using conductive silver filled epoxy, recommended epoxies are DieMat DM6030HK-PT/H579 or Ablestik 84-1LMISR4. Apply sufficient epoxy to meet required epoxy bond line thickness, epoxy fillet height and epoxy coverage around total die periphery. Parts shall be cured in a nitrogen filled atmosphere per manufacturer's cure condition. It is recommended to use antistatic die pick up tools only.

### 4. Wire Bonding

Bond pad openings in the surface passivation above the bond pads are provided to allow wire bonding to the dice gold bond pads. Thermosonic bonding is used with minimized ultrasonic content. Bond force, time, ultrasonic power and temperature are all critical parameters. Suggested wire is pure gold, 1 mil diameter. Bonds must be made from the bond pads on the die to the package or substrate. All bond wires should be kept as short as low as reasonable to minimize performance degradation due to undesirable series inductance.



Additional Detailed Technic additional information is available on our						
	Data Table	Data Table				
Performance Data	Swept Graphs	Swept Graphs				
	S-Parameter (S2P Files) Data Set with	S-Parameter (S2P Files) Data Set with and without port extension(.zip file)				
Case Style	Die					
	Quantity, Package	Model No.				
Die Ordering and packaging information	Small, Gel - Pak: 5,10,50,100 KGD* Medium <sup>†</sup> , Partial wafer: KGD*<3020 Large <sup>†</sup> , Full Wafer	MAR-8A-DG+ MAR-8A-DP+ MAR-8A-DF+				
momation	†Available upon request contact sales	†Available upon request contact sales representative				
	Refer to AN-60-067	Refer to <u>AN-60-067</u>				
Environmental Ratings	ENV80	ENV80				

<sup>\*</sup>Known Good Dice ("KGD") means that the dice in question have been subjected to Mini-Circuits DC test performance criteria and measurement instructions and that the parametric data of such dice fall within a predefined range. While DC testing is not definitive, it does help to provide a higher degree of confidence that dice are capable of meeting typical RF electrical parameters specified by Mini-Circuits.

# **ESD Rating\*\***

Human Body Model (HBM): Class 2 (2000V to <4000V) in accordance with ANSI/ESD STM 5.1 - 2001

### **Additional Notes**

- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
- B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.
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<sup>\*\*</sup> Measured on Mini-Circuits characterization test board. Die packaged in a plastic micro-x package and soldered on test board TB-432-8A+.